

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SK1341

Silicon N-Channel MOS FET

**RENESAS**

ADE-208-1278 (Z)

1st. Edition

Mar. 2001

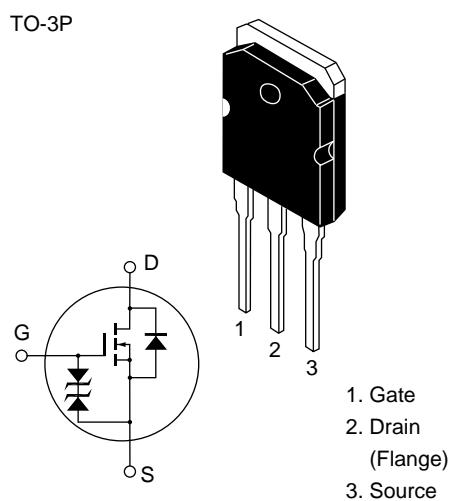
## Application

High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

## Outline



**Absolute Maximum Ratings (Ta = 25°C)**

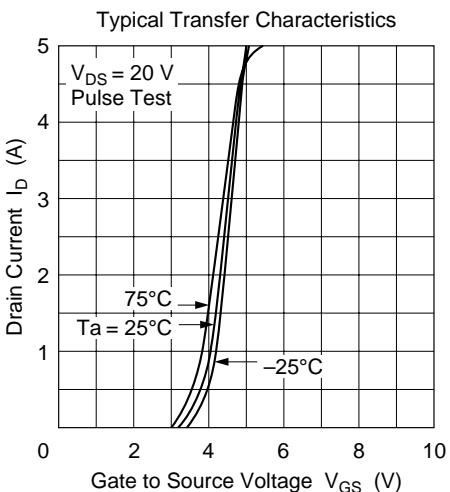
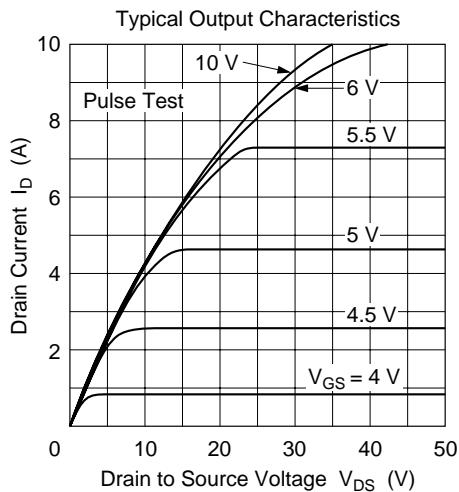
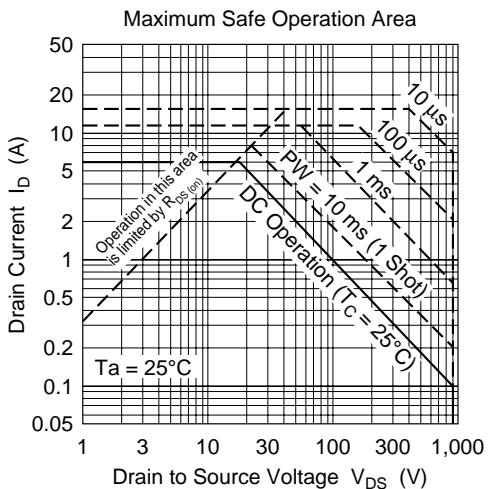
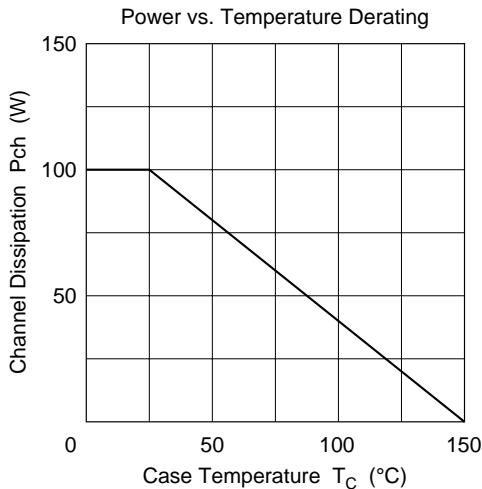
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	900	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	6	A
Drain peak current	I <sub>D(pulse)</sub> <sup>*1</sup>	15	A
Body to drain diode reverse drain current	I <sub>DR</sub>	6	A
Channel dissipation	Pch <sup>*2</sup>	100	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	−55 to +150	°C

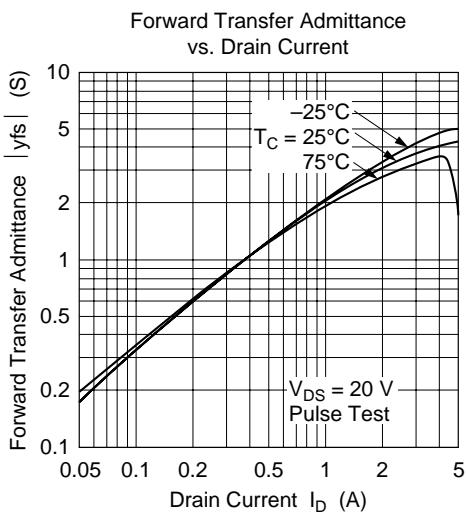
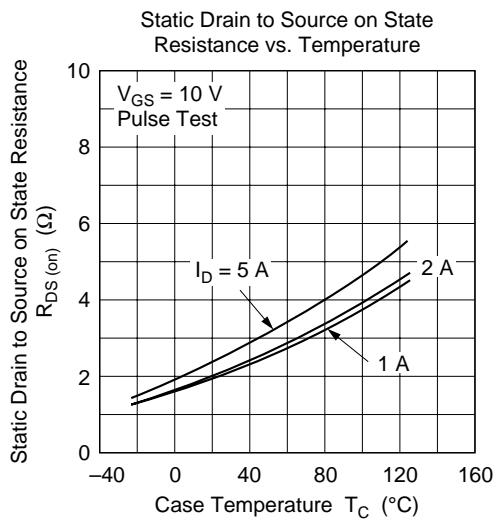
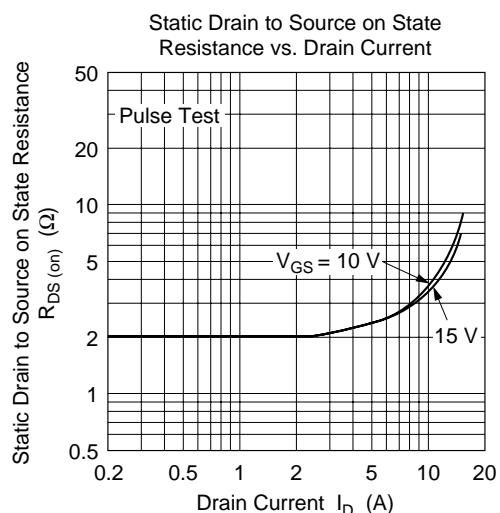
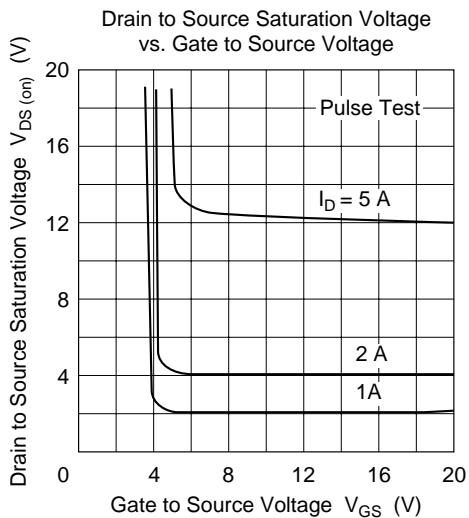
Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%  
2. Value at T<sub>c</sub> = 25°C

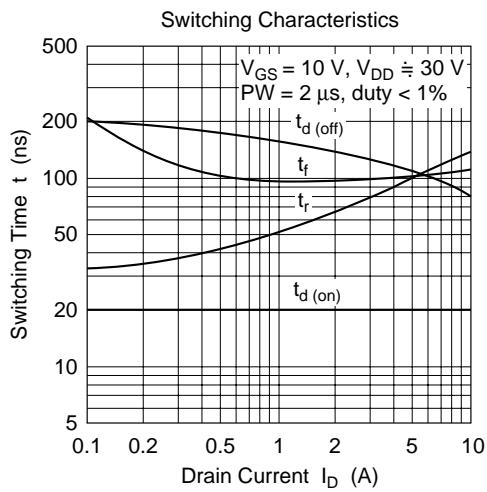
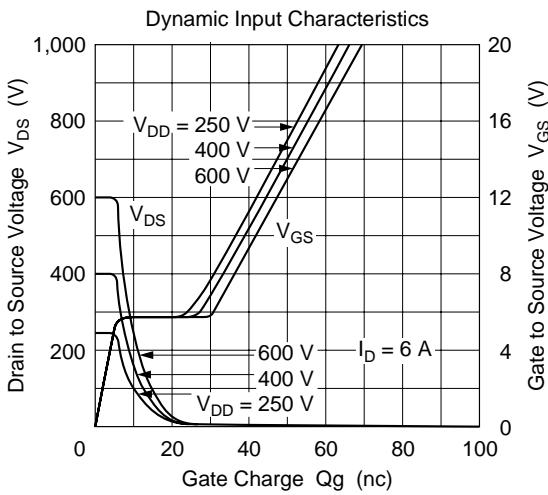
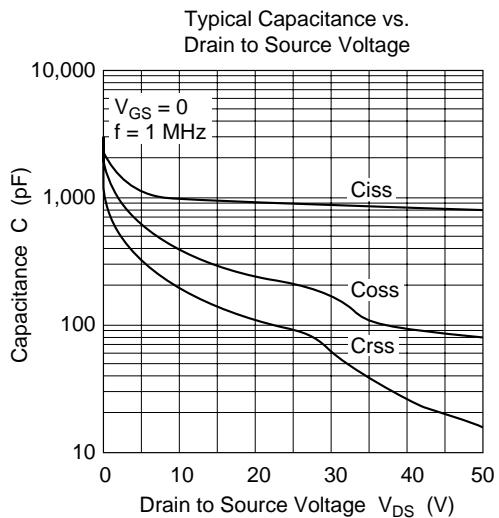
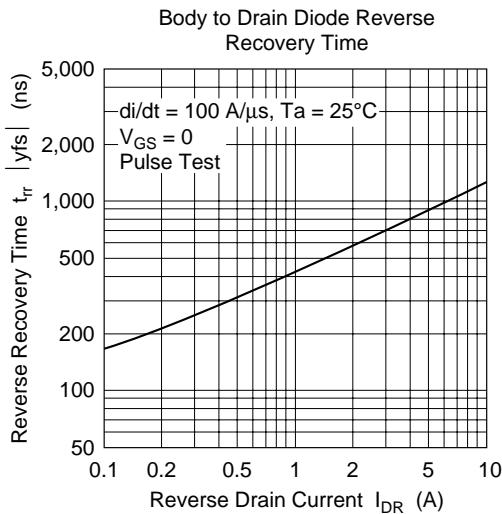
## Electrical Characteristics (Ta = 25°C)

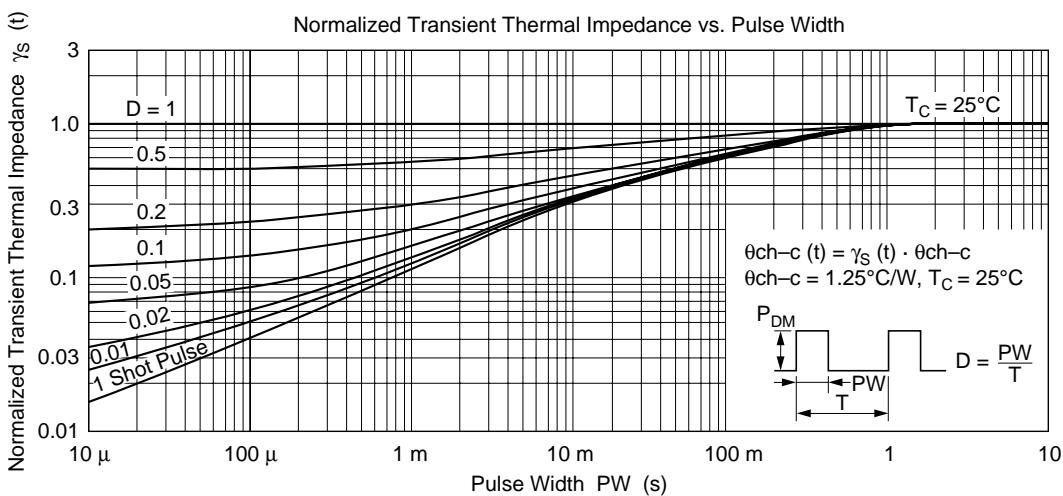
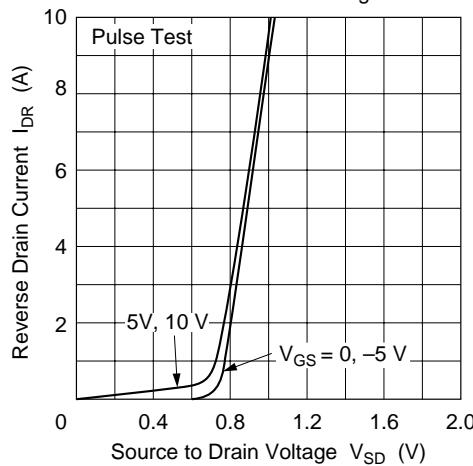
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	900	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±30	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	250	μA	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	3.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	2.0	3.0	Ω	I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V * <sup>1</sup>
Forward transfer admittance	y <sub>fs</sub>	2.3	3.7	—	S	I <sub>D</sub> = 3 A, V <sub>DS</sub> = 20 V * <sup>1</sup>
Input capacitance	C <sub>iss</sub>	—	980	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0,
Output capacitance	C <sub>oss</sub>	—	400	—	pF	f = 1 MHz
Reverse transfer capacitance	C <sub>rss</sub>	—	195	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	20	—	ns	I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V,
Rise time	t <sub>r</sub>	—	80	—	ns	R <sub>L</sub> = 10 Ω
Turn-off delay time	t <sub>d(off)</sub>	—	125	—	ns	
Fall time	t <sub>f</sub>	—	100	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	0.9	—	V	I <sub>F</sub> = 6 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	1000	—	ns	I <sub>F</sub> = 6 A, V <sub>GS</sub> = 0, di <sub>F</sub> /dt = 100 A/μs

Note: 1. Pulse test

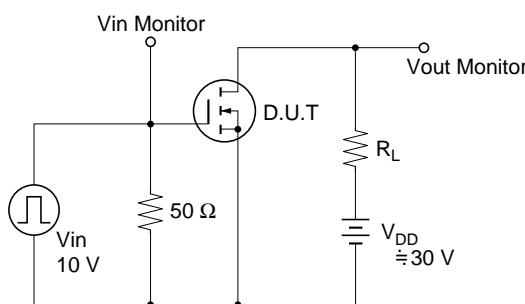




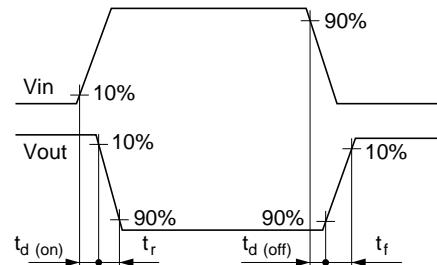


Reverse Drain Current vs.  
Source to Drain Voltage

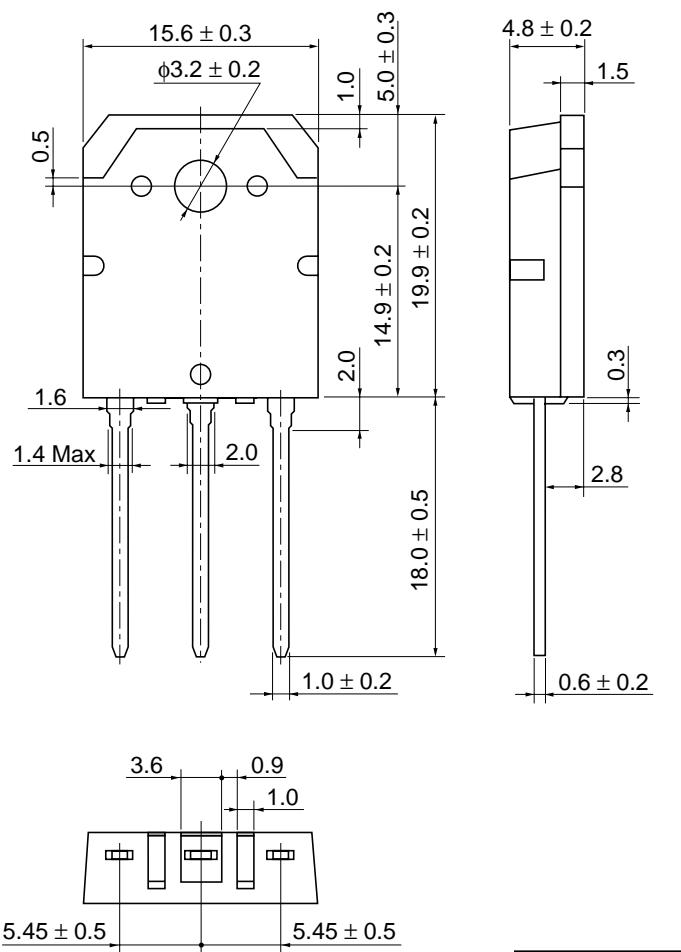
Switching Time Test Circuit



Waveforms

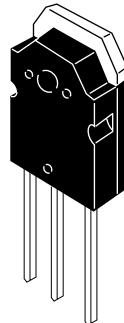


## Package Dimensions



As of January, 2001

Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

## Cautions

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